# MSKSEMI 美森科













**ESD** 

TVS

TSS

MOV

GDT

PLED

**L293DN(MS)** 

**Product specification** 





#### DESCRIPTION

The Device is a monolithic integrated high volt-age, high current four channel driver designed to accept standard DTL or TTL logic levels and drive inductive loads (such as relays solenoides, DC and stepping motors) and switching power tran- sistors. To simplify use as two bridges each pair of chan-nels is equipped with an enable input. A separate supply input is provided for the logic, allowing op-eration at a lower voltage and internal clamp di-odes are included.

This device is suitable for use in switching appli-cations at frequencies up to 5 kHz.

The L293DN(MS) is assembled in a 16 lead plastic packaage which has 4 center pins connected to- gether and used for heatsinking.

- 600mA OUTPUT CURRENT CAPABILITY PER CHANNEL
- 1.2A PEAK OUTPUT CURRENT (non repeti- tive) PER CHANNEL
- ENABLE FACILITY
- OVERTEMPERATURE PROTECTION
- LOGICAL "0" INPUT VOLTAGE UP TO 1.5 V (HIGH NOISE IMMUNITY)
- INTERNAL CLAMP DIODES

#### **Reference News**

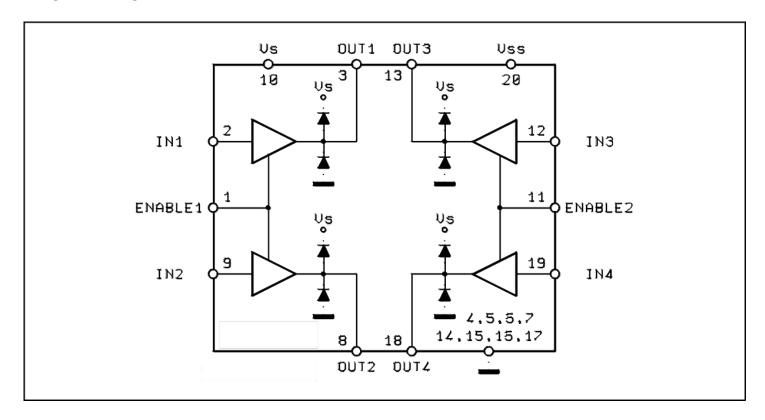
PACKAGE OUTLINE	Marking	
	MSKSEMI L293D MS****	
DIP-16		

#### ordering information

P/N	PKG	QTY	
L293DN(MS)	DIP-16	25/One tube 1000/a box of	



### **BLOCK DIAGRAM**

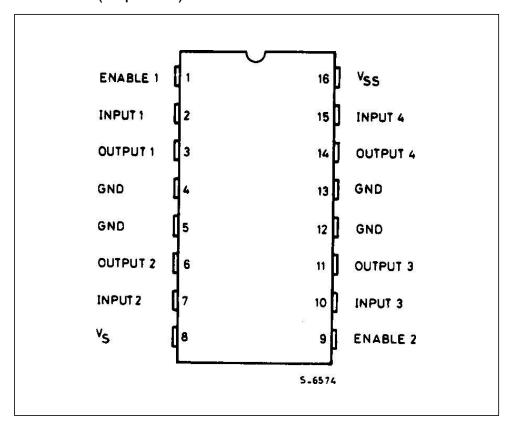


#### **ABSOLUTEMAXIMUMRATINGS**

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	36	V
V <sub>SS</sub>	Logic Supply Voltage	36	V
Vi	Input Voltage	7	V
Ven	Enable Voltage	7	V
lo	Peak Output Current (100 µs non repetitive)	1.2	Α
Ptot	Total Power Dissipation at T <sub>pins</sub> = 90 ℃	4	W
T <sub>stg</sub> , T <sub>j</sub>	Storage and Junction Temperature	– 40 to 150	${\mathbb C}$



# PIN CONNECTIONS (Top view)



#### THERMAL DATA

Symbol	Decription	DIP	Unit
Rth j-pins	Thermal Resistance Junction-pins max.	-	°C/W
Rth j-amb	Thermal Resistance junction-ambient max.	80	°C/W
Rth j-case	Thermal Resistance Junction-case max.	14	

<sup>(\*)</sup> With 6sq. cm on board heatsink.



# **ELECTRICAL CHARACTERISTICS** (for each channel, VS =24V, VSS =5 V, Tamb = 25°C, unless

otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Supply Voltage (pin 10)		Vss		36	V
Vss	Logic Supply Voltage (pin 20)		4.5		36	V
ls	T. 1.10 : 1.0 . 1.0	$V_i = L$ ; $I_O = 0$ ; $V_{en} = H$		2	6	mA
	Total Quiescent Supply Current (pin 10)	$V_i = H$ ; $I_0 = 0$ ; $V_{en} = H$		16	24	mA
	(ріп 10)	V <sub>en</sub> = L			4	mA
		$V_i = L$ ; $I_0 = 0$ ; $V_{en} = H$		44	60	mA
Iss	Total Quiescent Logic Supply Current (pin 20)	$V_i = H$ ; $I_0 = 0$ ; $V_{en} = H$		16	22	mA
	Current (pin 20)	Ven = L		16	24	mA
$V_{IL}$	Input Low Voltage (pin 2, 9, 12, 19)		- 0.3		1.5	٧
	Input High Voltage (pin 2, 9,	Vss < 7 V	2.3		Vss	V
V <sub>IH</sub>	12, 19)	V <sub>SS</sub> > 7 V	2.3		7	V
I <sub>IL</sub>	Low Voltage Input Current (pin 2, 9, 12, 19)	V <sub>IL</sub> = 1.5 V			- 10	μΑ
Ін	High Voltage Input Current (pin 2, 9, 12, 19)	2.3 V < V <sub>IH</sub> < V <sub>SS</sub> - 0.6 V		30	100	μΑ
Ven L	Enable Low Voltage (pin 1, 11)		- 0.3		1.5	V
.,	Enable High Voltage	Vss < 7 V	2.3		Vss	V
Ven H	(pin 1, 11)	V <sub>SS</sub> > 7 V	2.3		7	V
len L	Low Voltage Enable Current (pin 1, 11)	V <sub>en L</sub> = 1.5 V		- 30	- 100	μΑ
I <sub>en H</sub>	High Voltage Enable Current (pin 1, 11)	2.3 V < V <sub>en H</sub> < V <sub>SS</sub> - 0.6 V			± 10	μΑ
VCE(sat)H	Source Output Saturation Voltage (pins 3, 8, 13, 18)	I <sub>O</sub> = - 0.6 A		1.4	1.8	V
VCE(sat)L	Sink Output Saturation Voltage (pins 3, 8, 13, 18)	I <sub>O</sub> = + 0.6 A		1.2	1.8	V
VF	Clamp Diode Forward Voltage	I <sub>O</sub> = 600nA		1.3		V
t <sub>r</sub>	Rise Time (*)	0.1 to 0.9 V <sub>0</sub>		250		ns
t <sub>f</sub>	Fall Time (*)	0.9 to 0.1 V <sub>O</sub>		250		ns
ton	Turn-on Delay (*)	0.5 V <sub>i</sub> to 0.5 V <sub>O</sub>		750		ns
t <sub>off</sub>	Turn-off Delay (*)	0.5 V <sub>i</sub> to 0.5 V <sub>o</sub>		200		ns

<sup>(\*)</sup> See fig. 1.



# **TRUTH TABLE (one channel)**

Input	Enable (*)	Output
Н	Н	Н
L	Н	L
Н	L	Z
L	L	Z

Figure 1: Switching Times

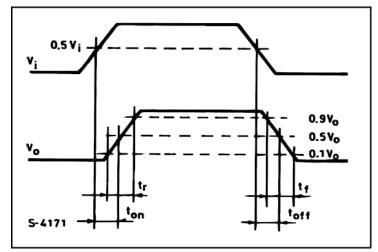
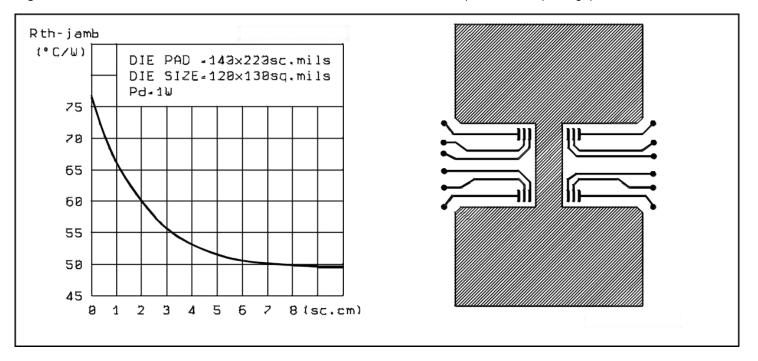


Figure 2: Junction to ambient thermal resistance vs. area on board heatsink (SO12+4+4 package)

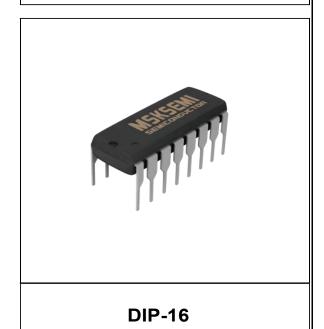


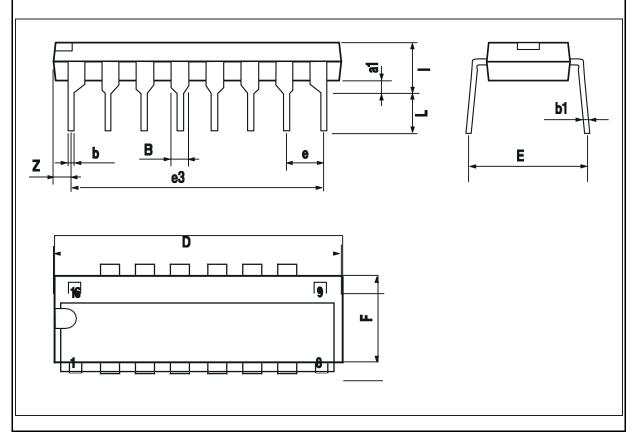
Z = High output impedance (\*) Relative to the considered channel



DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			20.0			0.787
E		8.80			0.346	
е		2.54			0.100	
e3		17.78			0.700	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050

# OUTLINE AND MECHANICAL DATA







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